TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7MH153FK

Dual 4 - Channel Multiplexer

The TC7MH153 is an advanced high speed CMOS DUAL 4-CHANNEL MULTIPLEXERs fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

Each of these data (1C0 - 1C3, 2C0 - 2C3) is selected by the two address inputs A and B.

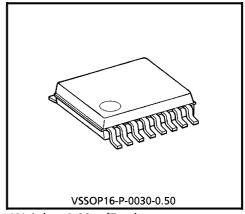
Separate strobe inputs $(1\overline{G}, 2\overline{G})$ are provided for each of the two four-line sections.

The strobe input (\overline{G}) can be used to inhibit the data output; the output is fixed in low level while the strobe input is held high.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features:

- High Speed······ $t_{pd} = 5.0$ ns(typ.) at $V_{CC} = 5V$
- Low Power Dissipation ············· $I_{CC} = 4\mu A(max)$ at $Ta = 25^{\circ}C$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range \cdots V_{CC} (opr) = $2V \sim 5.5V$
- Pin and Function Compatible with 74ALS153



Weight: 0.02g (Typ.)

IEC Logic Symbol

Pin Assignment								
1 G	1	Д ,	✓ b₁	6	V_{CC}			
В	2	d	1	5	$2\overline{G}$			
1C3	3	d	<u></u> 1	4	Α			
1C2	4	П	1	3	2C3			
1C1	5	Д	<u></u> 1	2	2C2			
1C0	6	3	<u> </u>	1	2C1			
1Y	7	Д	<u></u> 1	0	2C0			
GND	8	8	<u></u> 9)	2Y			
		(TOP	VIEW)					

Truth Table

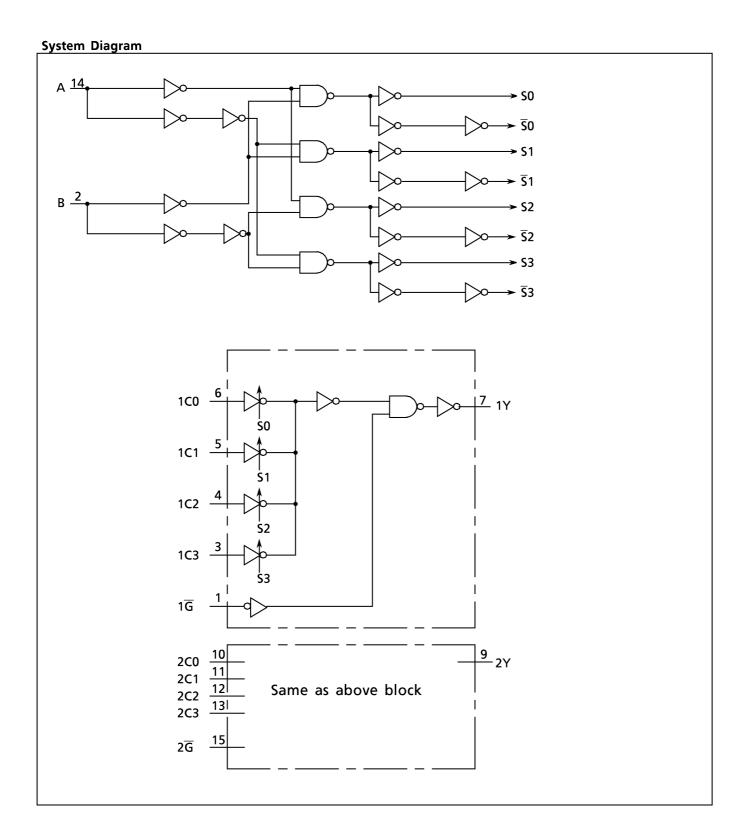
	ECT UTS	I	DATA	INPUTS	;	STROBE	OUTPUTS Y L L H
В	Α	C 0	C 1	C 2	C 3	G	Υ
X	Х	Х	Х	Х	Х	Н	L
L	L	L	Х	Х	Х	L	L
L	L	Н	Х	Х	Х	L	Н
L	Н	Х	L	Х	Х	L	L
L	Н	Х	Н	Х	Х	L	Н
Н	L	Х	Х	L	Х	L	L
Н	L	Х	Х	Н	Х	L	Н
Н	Н	Х	Х	Х	L	L	L
Н	Н	Х	Х	Х	Н	L	Н

X: Don't Care

2C2⁽¹²⁾ 2C3⁽¹³⁾

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Absolute Maximum Ratings

-			
PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	− 0.5~7.0	V
DC Input Voltage	VIN	− 0.5~7.0	V
DC Output Voltage	V _{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current	I _{OK}	±20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} /Ground Current	I _{CC}	± 50	mA
Power Dissipation	P _D	180	mW
Storage Temperature	T _{stg}	−65~150	°C

Recommended Operating Conditions

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{cc}	2.0~5.5	V
Input Voltage	V _{IN}	0~5.5	٧
Output Voltage	V _{OUT}	0~V _{cc}	٧
Operating Temperature	T _{opr}	−40~85	°C
Input Rise and Fall Time	dt/dv	$0 \sim 100 \text{ (Vcc} = 3.3 \pm 0.3 \text{V)}$ $0 \sim 20 \text{ (Vcc} = 5 \pm 0.5 \text{V)}$	ns / V

DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CO	NDITION	$V_{CC} = Ta = 25^{\circ}C \qquad Ta = -40^{\circ}85^{\circ}C$		10∼85°C	UNIT			
FARAIVIETER	STIVIBUL	TEST CONDITION		(V)	Min	Тур.	Max	Min	Max	CIVII
High - Level	V _{IH}			2.0 3.0~	1.50	_	_	1.50		<
Input Voltage	*118				$V_{cc} \times 0.7$	_	_	$V_{cc} \times 0.7$,
Low - Level	.,			2.0	_	_	0.50	_	0.50	
Input Voltage	V _{IL}			3.0~ 5.5	_	_	$V_{cc} \times 0.3$	_	$V_{cc} \times 0.3$	^
		W	FO A	2.0 3.0	1.9 2.9	2.0 3.0		1.9 2.9		
High - Level Output Voltage	V _{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50\mu A$	4.5	4.4	4.5	_	4.4	_	v
			$I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94	_	_	2.48 3.80		
Low - Level Output Voltage	V _{OL}	V _{1 N} =	$I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1	_ _ _	0.1 0.1 0.1	٧
		V _{IH} or V _{IL}	$I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5		_	0.36 0.36	_	0.44 0.44	
Input Leakage Current	I _{IN}	V _{IN} = 5.5V or GND		0~5.5	_		±0.1	_	± 1.0	
Quiescent Supply Current	I _{cc}	$V_{IN} = V_{CC}$ or GND		5.5	-	_	4.0	_	40.0	μ A

AC	Electrical	Characteristics ($(Input t_r = t_f = 3ns)$
AC	Electrical	Characteristics	(input t _r = t _f = 5n5

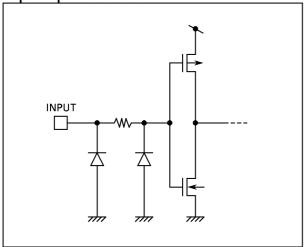
PARAMETER	SYMBOL	TES	CONDITI	ON		Га = 25°C	-	Ta = - 4	UNIT	
FARAIVIETER	STIVIBUL		V _{CC} (V)	CL (pF)	Min	Тур.	Max	Min	Max	
			3.3 ± 0.3	15	-	7.7	11.9	1.0	14.0	
Propagation Delay Time	t _{pLH}	3.3 ± 0.3	50	1	10.2	15.4	1.0	17.5		
(Cn-Y)	t_{pHL}		5.0 ± 0.5	_E 15 - 5.0 7.7	7.7	1.0	9.0			
(,			3.0 ± 0.5	50	1	6.5	9.7	1.0	11.0	
			3.3 ± 0.3	15	1	10.8	16.7	1.0	19.5	ns
Propagation Delay Time	$t_{ m pLH}$			50	1	13.3	20.2	1.0	23.0	
(A,B-Y)	t_pHL		5.0 ± 0.5	15	_	6.8	9.9	1.0	11.5	
(, , , _ , ,			15.5 2 6.5	50	1	8.3	11.9	1.0	13.5	
			3.3 ± 0.3	15	1	6.3	10.1	1.0	12.0	
Propagation Delay Time	t_{pLH}		3.3 ± 0.3	50	_	8.8	13.6	1.0	15.5	
(G -Y)	t _{pHL}		1.0	7.5						
(- 1)			3.0 ± 0.5	50	_	5.9	8.4	1.0	9.5	
Input Capacitance	C _{I N}				_	4	10	_	10	
Power Dissipation Capacitance	C _{PD}		(Note 1)		_	20	-	_	_	pF

(Note 1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC\,(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

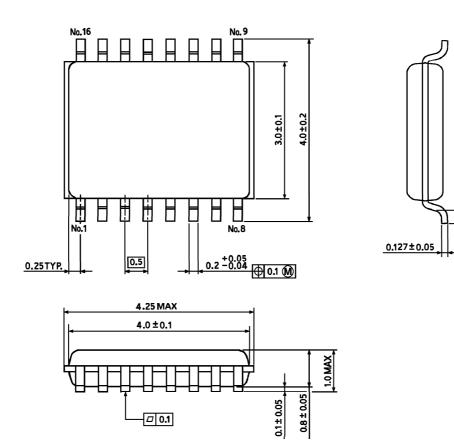
$$I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$





Unit: mm

Outline Drawing VSSOP16-P-0030-0.50



□ 0.1

Weight: 0.02g (Typ.)